

# 5V, R/W Preamplifier for 2 Terminal Recording Heads, 2 or 4 Channels

## **GENERAL DESCRIPTION**

The XR-9030/9030R are bipolar monolithic integrated circuits commonly used in two terminal thin film recording head applications. The circuitry on the device includes a low noise preamplifier, write current control circuitry and data protection. It is available for both two and four channel applications. Power supply fault detection circuitry present on the device disables the write current generator in various power down modes. The read recovery time is improved by control of the read channel common mode output shift when in write mode. The read write device in the XR-9030R option offers internal 700 Ohm damping resistors.

The XR-9030 operates on a single 5V power supply making it ideal for low power applications. Both versions are available in a variety of low profile packaging options.

## **FEATURES**

5V Supply Voltage Only Low Power Device (150mW Typ in Read mode) High Performance Circuitry

- -Low Input Noise = 0.85nV/\Hz max
- -Read Mode Gain = 200V/V
- -Input Capacitance = 35pF max
- -Write Current Range = 2-35mA

Programmable Write Current Source
Write Unsafe Detect/Indicator
Power Supply Fault Protection
Head Short to Ground Protection
Enhanced Write to Read Recovery Time
Designed for Use With Two Terminal Thin Film Heads

## **APPLICATIONS**

Thin Film Recording Heads in Hard Disk Drives

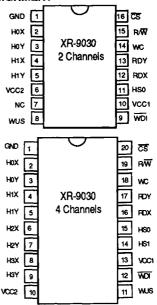
## **ABSOLUTE MAXIMUM RATINGS**

DC Supply Voltage
Write Current IW
Digital Input Voltage
Head Port Voltage
-0.3 to VCC1 +0.3 VDC
-0.3 to VCC2 +0.3 VDC

Output Current Maximum

Pins: RDX, RDY ±10mA WUS +12mA Storage Temperature Range -65°C to +150°C

#### **PIN ASSIGNMENT**



## **ORDERING INFORMATION**

Part Number	Package	Operating Temperature
XR-9030/9030R-4D	20 Pin SOP	0°C to 70°C
XR-9030/9030R-2D	16 Pin SOP	0°C to 70°C
XR-9030/9030R-4D	20 Pin SSO	P 0°C to 70°C

## SYSTEM DESCRIPTION

The XR-9030/9030R is a low power, two or four channel hard disk drive Read / Write preamplifier for thin film (2 terminal) heads. The XR-9030/9030R provides superior recording performance, and uses only a +5V power supply. Its low power consumption suits it for drives used in battery powered laptop computers. The read amplifier consists of a 60 MHz bandwidth 0.55 nV/\Hz input noise (both typical) differential amplifier with a fixed gain of 200 V/V. The write driver has a current range of 2 to 35 mA and is disabled automatically when a voltage fault is detected. The write mode also has a write unsafe detection circuit.

# **ELECTRICAL CHARACTERISTICS**

Test Conditions: LH = 1.0 $\mu$ H RH = 30  $\Omega$ , I<sub>W</sub> = 20mA, f(Data) = 5MHz, V<sub>CC1</sub> = V<sub>CC2</sub> = 5V  $\pm$ 5%

	PARAMETERS	MIN	TYP	MAX	UNITS	CONDITIONS
DIGITAL IN	IPUTS			·		
VIL VIH	Input Low Voltage Input High Voltage Input Low Current	2.0		0.8	V V μΑ	VIL = 0.8V
IIH WUS VOL VF	Input High Current WUS Output Low Voltage VCC1 Fault Voltage			100 0.5 4.2	μA V V	VIH = 2.0V IoL = 2mA Note 1
VF	Fault to No Fault VCC1 Fault Voltage No Fault to Fault	3.8			v	
WRITE CH	ARACTERISTICS		I			
Vwc	Write Current Voltage Differential Head Voltage Swing Unselected Head Current Head Differential Load Capacitance	1.15 3.4		1.35 1 25	V V mA pk	
	Head Differential Load Resistance Head Differential Load Resistance WDI Transition Frequency	560 4K 1	700	950	, MHz	R Option  lw = 5mA
	1					71
lw	Write Current Range	2		35	mA D	(BDV BDV)
READ CHAI	Write Current Range  RACTERISTICS Recommended operation  RDX,RDY) <20 pF, f = 5MHz  Differential Voltage Gain		is apply, uni			L(RDX,RDY)
READ CHAI = 1KΩ, C <sub>L</sub> (I Av BW	RACTERISTICS Recommended operation RDX,RDY) <20 pF, f = 5MHz	ng condition		ess otherwi	se stated. R	BW= 15 MHz L <sub>H</sub> = 0,
READ CHAI = 1KΩ, CL(I Av BW eni	RACTERISTICS Recommended operation RDX,RDY) <20 pF, f = 5MHz  Differential Voltage Gain Bandwidth -3dB Equivalent Input Noise  Differential Input Capacitance	ng condition	200 60 0.55	ess otherwi	se stated. R  V/V  MHz  nV/√Hz  pF	BW= 15 MHz L <sub>H</sub> = 0,
READ CHAI = 1KΩ, CL(I Av BW eni CIN RIN	RACTERISTICS Recommended operation RDX,RDY) <20 pF, f = 5MHz  Differential Voltage Gain Bandwidth -3dB Equivalent Input Noise  Differential Input Capacitance Differential Input Resistance	ng condition	200 60 0.55	240 0.85	se stated. R  V/V  MHz  nV/√Hz  pF  Ω	BW= 15 MHz L <sub>H</sub> = 0, R <sub>H</sub> = 0
READ CHAI = 1KΩ, CL(I Av BW eni CIN RIN RIN	RACTERISTICS Recommended operation RDX,RDY) <20 pF, f = 5MHz  Differential Voltage Gain Bandwidth -3dB Equivalent Input Noise  Differential Input Capacitance Differential Input Resistance Differential Input Resistance Dynamic Range to 90% of Gain	160 35 835	200 60 0.55	240 0.85	se stated. R  V/V  MHz  nV/√Hz  pF  Ω  mV pp	BW= 15 MHz L <sub>H</sub> = 0,
READ CHAI = 1KΩ, CL(I Av BW eni CIN RIN RIN CMRR	RACTERISTICS Recommended operation RDX,RDY) <20 pF, f = 5MHz  Differential Voltage Gain Bandwidth -3dB Equivalent Input Noise  Differential Input Capacitance Differential Input Resistance Differential Input Resistance	160 35 835	200 60 0.55	240 0.85	se stated. R  V/V  MHz  nV/√Hz  pF  Ω Ω	BW= 15 MHz L <sub>H</sub> = 0, R <sub>H</sub> = 0  R Option  100mV <sub>DD</sub> 5MHz sin
READ CHAI = 1KΩ, CL(I Av BW eni CIN RIN	RACTERISTICS Recommended operation RDX,RDY) <20 pF, f = 5MHz  Differential Voltage Gain Bandwidth -3dB Equivalent Input Noise  Differential Input Capacitance Differential Input Resistance Differential Input Resistance Dynamic Range to 90% of Gain Common Mode Rejection Ratio	160 35 835	200 60 0.55	240 0.85	se stated. R  V/V  MHz  nV/√Hz  pF  Ω  Ω  mV pp  dB	BW= 15 MHz L <sub>H</sub> = 0, R <sub>H</sub> = 0 R Option
READ CHAI = 1KΩ, CL(I Av BW eni CIN RIN RIN CMRR	RACTERISTICS Recommended operation RDX,RDY) <20 pF, f = 5MHz  Differential Voltage Gain Bandwidth -3dB Equivalent Input Noise  Differential Input Capacitance Differential Input Resistance Differential Input Resistance Dynamic Range to 90% of Gain Common Mode Rejection Ratio Power Supply Rejection Ration	160 35 835 3 45 40	200 60 0.55	240 0.85	se stated. R  V/V  MHz  nV/√Hz  pF  Ω  Ω  mV pp  dB  dB	BW= 15 MHz L <sub>H</sub> = 0, RH = 0  R Option  100mV <sub>pp</sub> 5MHz sin on V <sub>CC</sub> Unselected channels driven with100mV <sub>pp</sub>

## DC CHARACTERISTICS

SYMBOL	PARAMETERS	MIN	TYP	MAX	UNITS	CONDITIONS
I <sub>CC</sub> 1	VCC1 Supply Current			33	mA	READ Mode
				27	mA	WRITE Mode
				12	mA	IDLE Mode
lcc2	VCC2 Supply Current			11	mA	READ Mode
				10+ IW	mA	WRITE Mode
				400	μΑ	IDLE Mode
P <sub>D</sub>	Power Dissipation			230	mW	READ Mode
				190+4IW	l mW	WRITE Mode
			35	45	mW	IDLE Mode

Note 1: On the Fault to No Fault transition, all devices will be No Fault at 4.2V.
On the No Fault to Fault transition, all devices will be Fault at 3.8V.

SWITCHING CHARACTERISTICS - Recommended operating conditions apply unless otherwise specified. lw = 20 mA, Lh = 1.0  $\mu$ H, Rh = 30 $\Omega$ , f(Data) = 5 MHz

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	CONDITIONS
	R/W Read to Write		0.1	1.0	μs	R/W to 90% of write
	Write to Read		0.5	1.0	μs	R/W to 90% of 100mV 10 MHz Read signal envelope
	CS Unselect to Select		0.4	1.0	μs	CS to 90% of write current or to 90% of 100mV 10MHz Read signal envelope
	Select to Unselect		0.4	1.0	μs	CS to 10% of write current
	HS0,1 to any Head		0.2	1.0	μs	To 90% of 100mV 10MHz Read signal envelope
TD1	WUS: Safe to Unsafe	0.6	2.0	3.6	μs	
TD2	Unsafe to Safe		0.2	1.0	μs	
	Head Current:					Lh = 0, Rh = 0
TD3	WDI to Ix - Iy Asymmetry			32	ns	from 50% level
	Asymmetry			1.0	ns	WDI has 1 ns rise/fall time
	Rise/Fall Time			12	ns	10% to 90% level

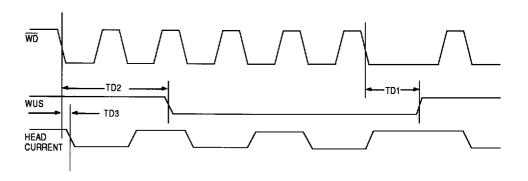


Figure 1. Write Mode Timing Diagram

# PIN DESCRIPTION

Pin#	Symbol	1/0	Description	Pin#	Symbol I	<b>/O</b>	Description
14,15 i	HS0,HS1	1	Head Select. Select one of four heads.		HOY-H3X; 1 HOY-H3Y	VO	X,Y Head Connections
20	CS	l	Chip Select. High inhibits the chip.	16,17R	DX, RDY*	0	X,Y Read Data. Differential read data output.
19	R/W	i	Read/Write. High selects Read mode.	18	wc		Write Current. Used to set the magnitude of the write current.
11	wus*	0	Write Unsafe. High indicates an unsafe writing condition.	13	VCC1	1	+5V Supply
12	WDI	ı	Write Data In. Changes the direction of the current in the	10	VCC2	l	+5V Supply for Write current drivers.
			recording head.	1	GND	I	Ground

<sup>\*</sup> These signals can be wire OR'ed.

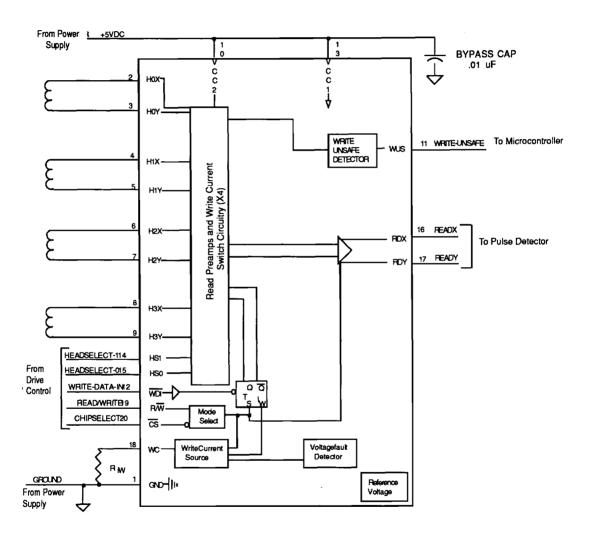


Figure 2. IC Interconnection and Block Diagram

## CIRCUIT OPERATION

The XR-9030/9030R read/write device is intended for use in thin film head hard disk drives with up to four heads. Head selection and mode selection instructions are shown in Tables 1 and 2 respectively. The TTL inputs  $\overline{R/W}$  and  $\overline{CS}$  protect from accidental write current by internal pull up resistors. HSO and HS1 have internal pull down resistors. The pin descriptions are shown on page 4.

#### Read Mode

In read mode operation, the low noise preamplifier circuit reads and amplifies pulses detected on the disk surface caused by magnetic transitions in the media. In this mode write current operations are disabled. RDX and RDY are emitter follower outputs which provide differential read data output pulses. These should be AC coupled to the load. In Write mode and in Idle mode these outputs go into a high impedance state. This allows wire-oring of these outputs in multi-chip applications where more than four head capability is required.

### Write Mode

Write mode is selected when both RW and  $\overline{CS}$  are taken low. The head current direction of the selected head is toggled by each negative going transition on the write data input pin,  $\overline{WDI}$ . A preceding read or idle mode select initializes the write data flip-flop to pass current through the X side of the head. This current is set by and external resistor, Rw, where:

#### MODE DESCRIPTION

HS1	HSO	Head
0	0	0
0	1	1
11	0	2
1	1	3

Rw is connected between the pins WC and GND. The actual head current is also a function of the head resistance and external wire resistance (Rh) and the damping resistance (Rd), so that:

$$ix,y = \frac{iw}{1 + Rh/Rd}$$

The write unsafe detector is also activated in this state.

The pin WUS is an open collector output which should be tied to VCC by a  $2K\Omega$  to  $10K\Omega$  resistor.

#### Idle Mode

This mode is selected by taking the pin  $\overline{CS}$  high. The pins RDX and RDY are placed in a high impedance mode to minimize device power consumption and allow another chip to drive these common lines.

## Voltage Fault

The write current function is disabled when either a voltage fault or power startup mode is detected, to avoid going into Write mode and contaminating the disks.

The following conditions will indicate a Write Unsafe, but will not stop the Write operation:

- -Device in Read Mode
- -Chip Disabled
- -WDI Frequency too Low
- -No Write Current
- -Head Opened

•		
<u>cs</u>	R/W	Mode
0	0	Write
0	1	Read
1	_ o	idle
1	1	ldle

Table 2. Mode Select